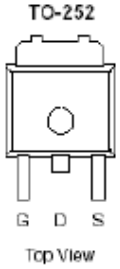
N-Channel 100-V (D-S) MOSFET

Key Features:
- Low $r_{DS(on)}$ trench technology
- Low thermal impedance
- Fast switching speed

PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (mΩ)	I_D(A)
100	50 @ V_{GS} = 10V	26
	59 @ V_{GS} = 4.5V	24

Typical Applications:
- PoE Power Sourcing Equipment
- PoE Powered Devices
- Telecom DC/DC converters
- White LED boost converters

Pb-free
RoHS COMPLIANT
HALOGEN FREE



ABSOLUTE MAXIMUM RATINGS (T_A = 25°C UNLESS OTHERWISE NOTED)				
Parameter		**Symbol**	**Limit**	**Units**
Drain-Source Voltage		V_{DS}	100	V
Gate-Source Voltage		V_{GS}	±20	
Continuous Drain Current	T_C=25°C	I_D	26	A
Pulsed Drain Current [b]		I_{DM}	100	
Continuous Source Current (Diode Conduction)		I_S	49	A
Power Dissipation	T_C=25°C	P_D	50	W
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 175	°C

THERMAL RESISTANCE RATINGS			
Parameter	**Symbol**	**Maximum**	**Units**
Maximum Junction-to-Ambient [a]	$R_{\theta JA}$	40	°C/W
Maximum Junction-to-Case	$R_{\theta JC}$	3	

Notes

a. Surface Mounted on 1” x 1” FR4 Board.

b. Pulse width limited by maximum junction temperature

Typical Electrical Characteristics

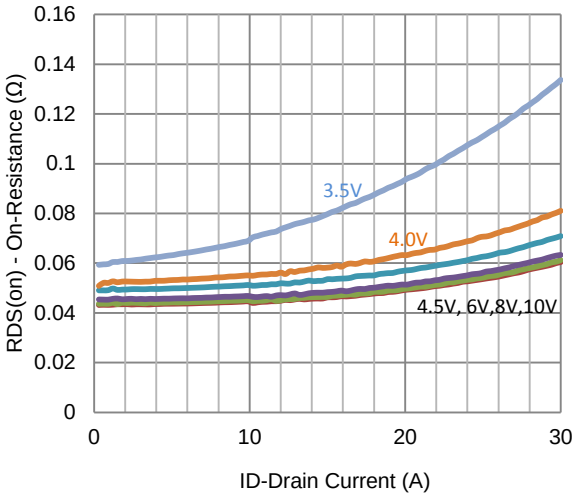
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static						
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 uA	1			V
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±20 V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 80 V, V_{GS} = 0 V			1	uA
		V_{DS} = 80 V, V_{GS} = 0 V, T_J = 55°C			10	
On-State Drain Current	$I_{D(on)}$	V_{DS} = 5 V, V_{GS} = 10 V	13			A
Drain-Source On-Resistance	$r_{DS(on)}$	V_{GS} = 10 V, I_D = 13 A			50	mΩ
		V_{GS} = 4.5 V, I_D = 12 A			59	
Forward Transconductance	g_{fs}	V_{DS} = 15 V, I_D = 13 A		8		S
Diode Forward Voltage	V_{SD}	I_S = 24 A, V_{GS} = 0 V		0.9		V
Dynamic						
Total Gate Charge	Q_g	V_{DS} = 50 V, V_{GS} = 10 V, I_D = 13 A		15		nC
Gate-Source Charge	Q_{gs}			3.9		
Gate-Drain Charge	Q_{gd}			9		
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 50 V, R_L = 3.8 Ω , I_D = 13 A, V_{GEN} = 10 V, R_{GEN} = 6 Ω		5		ns
Rise Time	t_r			11		
Turn-Off Delay Time	$t_{d(off)}$			43		
Fall Time	t_f			24		
Input Capacitance	C_{iss}	V_{DS} = 15 V, V_{GS} = 0 V, f =1 MHz		1067		pF
Output Capacitance	C_{oss}			118		
Reverse Transfer Capacitance	C_{rss}			107		

Notes

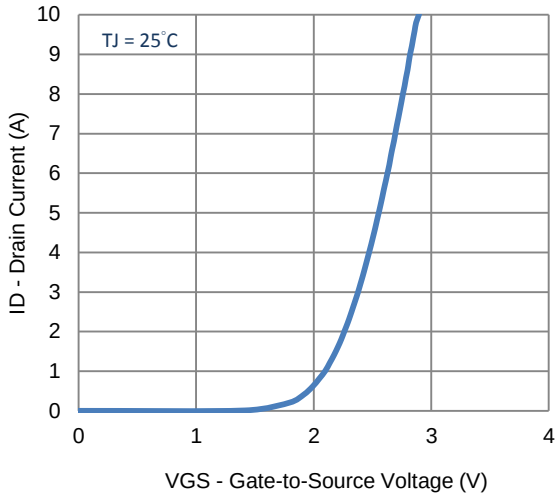
a. Pulse test: PW <= 300us duty cycle <= 2%.

b. Guaranteed by design, not subject to production testing.

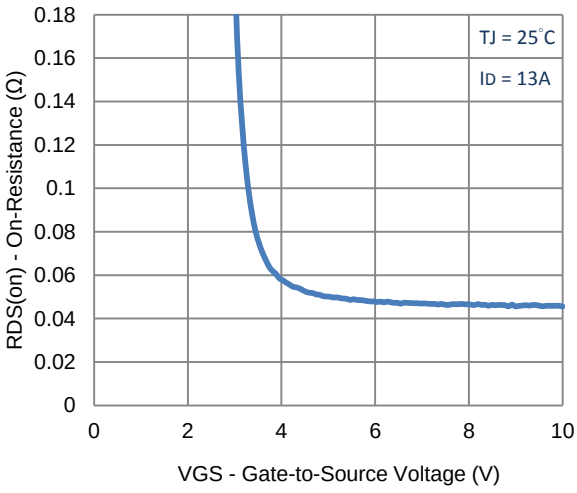
Typical Electrical Characteristics



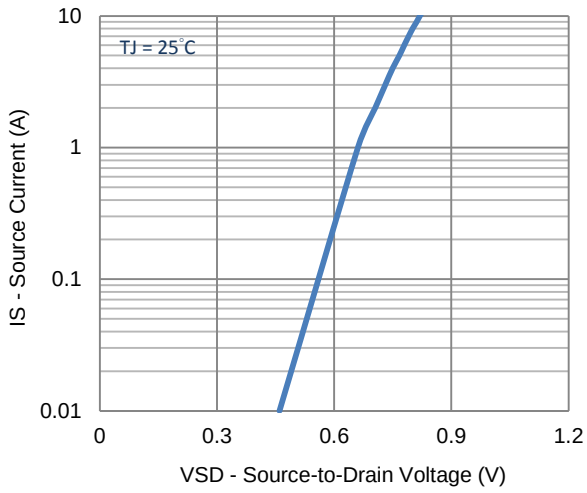
1. On-Resistance vs. Drain Current



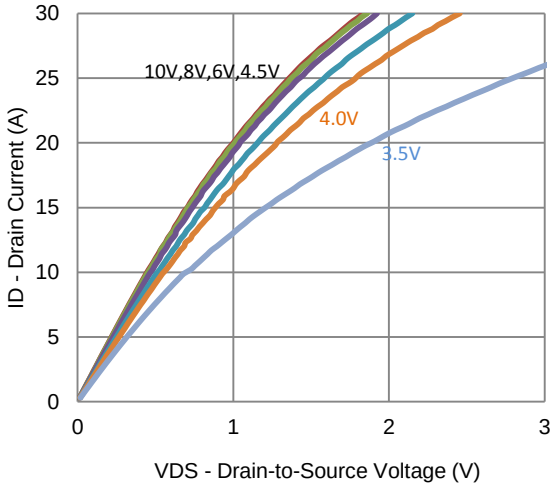
2. Transfer Characteristics



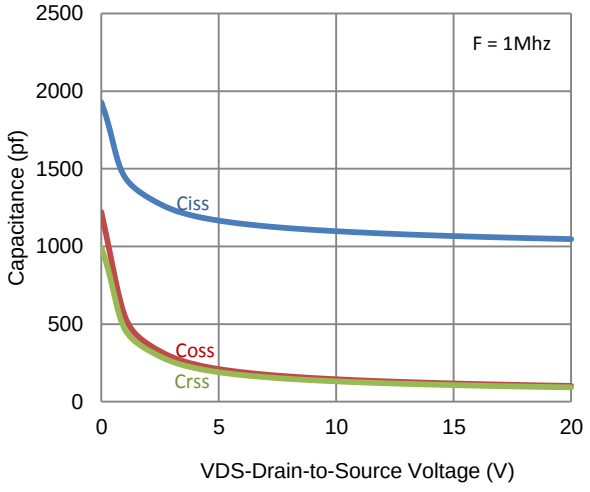
3. On-Resistance vs. Gate-to-Source Voltage



4. Drain-to-Source Forward Voltage

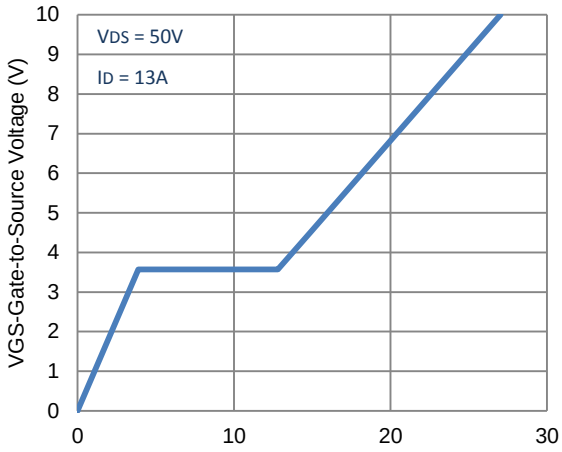


5. Output Characteristics

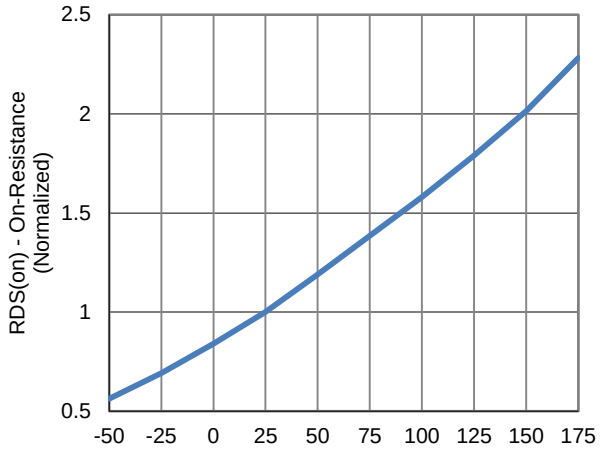


6. Capacitance

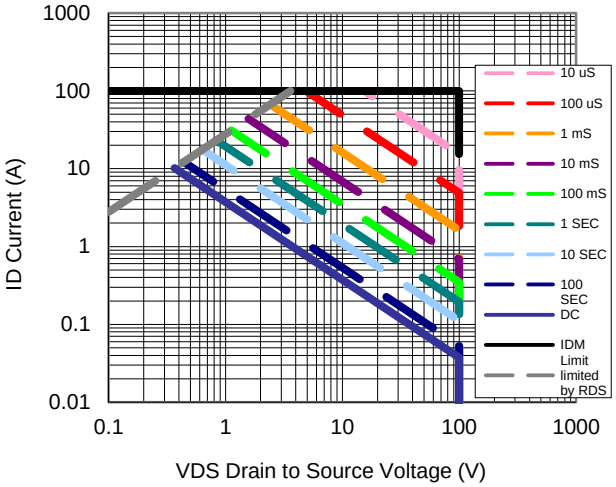
Typical Electrical Characteristics



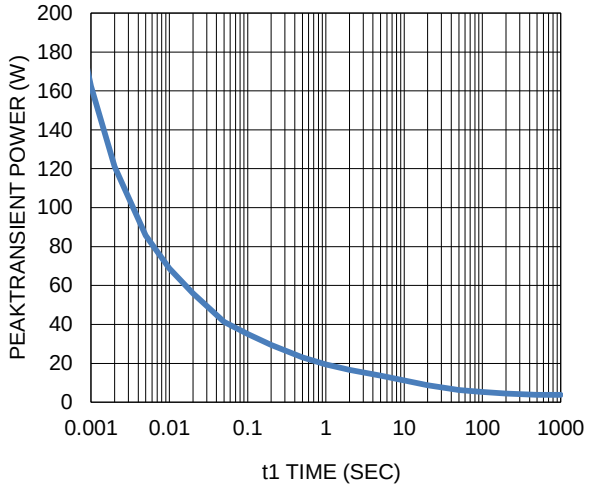
7. Gate Charge



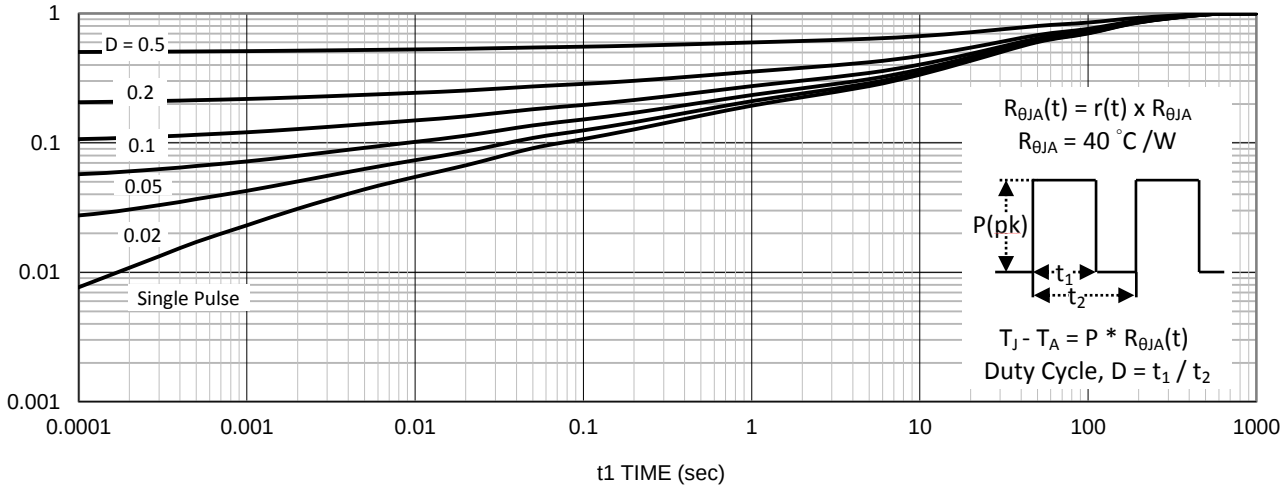
8. Normalized On-Resistance Vs Junction Temperature



9. Safe Operating Area

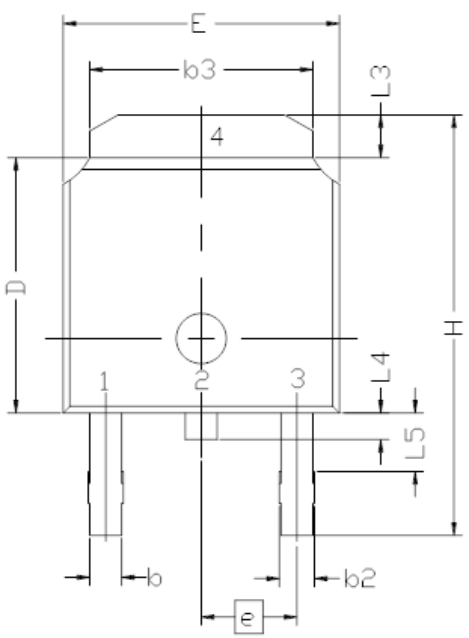


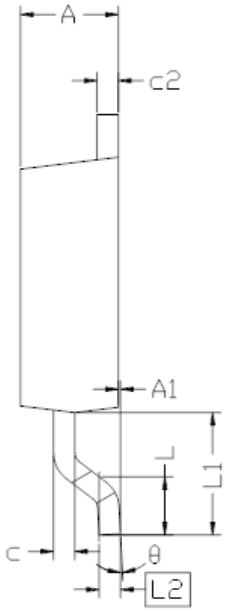
10. Single Pulse Maximum Power Dissipation

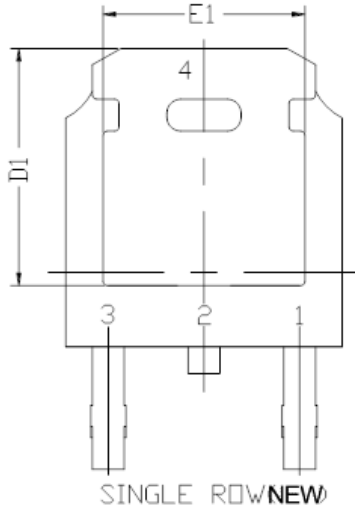


11. Normalized Thermal Transient Junction to Ambient

Package Information







SYMBOL	DIMENSIONAL REQMTS		
	MIN	NOM	MAX
E	6.40	6.60	6.731
L	1.40	1.52	1.77
L1	2.743 REF		
L2	0.508 BSC		
L3	0.89	--	1.27
L4	0.64	--	1.01
L5	--	--	--
D	6.00	6.10	6.223
H	9.40	10.00	10.40
b	0.64	0.76	0.88
b2	0.77	0.84	1.14
b3	5.21	5.34	5.46
e	2.286 BSC		
A	2.20	2.30	2.38
A1	0	--	0.127
c	0.45	0.50	0.60
c2	0.45	0.50	0.58
D1	5.30	--	--
E1	4.40	--	--
θ	0°	--	10°

Note:
1. All Dimension Are In mm.
2. Package Body Sizes Exclude Mold Flash, Protrusion Or Gate Burrs. Mold Flash, Protrusion Or Gate Burrs Shall Not Exceed 0.10 mm Per Side.
3. Package Body Sizes Determined At The Outermost Extremes Of The Plastic Body Exclusive Of Mold Flash, Gate Burrs And Interlead Flash, But Including Any Mismatch Between The Top And Bottom Of The Plastic Body.